Curriculum & Syllabus

of

M.Tech. Nanoscience and Technology

(For the batch admitted in 2010-11 onwards)



K.S.RANGASAMY COLLEGE OF TECHNOLOGY TIRUCHENGODE – 637 215

(An Autonomous Institution affiliated to Anna University Chennai and approved by AICTE New Delhi)

K.S. Rangasamy Colle Autonomous	R 2010	
Department	echnology	
Programme Code & Name	PNT: M.Tech. Nanos Technology	

K.S. Rangasamy College of Technology, Tiruchengode 637 215									
	Curricul	um for the programmes	unde	r Auto	nomou	s Scheme			
Regulation		R 2010							
Department		Department of Nanos	science and Technology						
Programme Code & Name PNT: M.Tech. Nanos			cience	and T	echnol	ogy			
	Semester I								
Course Code	Cours	se Name	Ho	urs/ W	eek	Credit	Ma	aximum	Marks
	Cours	se Name	L	Т	Р	С	CA	ES	Total
THEORY									
10 PNT 101	Applied Numerical		3	1	0	4	50	50	100
10 PNT 102	Quantum Concept		3	1	0	4	50	50	100
10 PNT 103	Introduction to Na Technology		3	0	0	3	50	50	100
10 PNT 104	Advanced Materia	••	3	1	0	4	50	50	100
10 PNT 105	Introduction to Bio	materials	3	0	0	3	50	50	100
10 PNT 106	Computer Program	nme in C and C++	3	0	0	3	50	50	100
PRACTICAL									
10 PNT 107	Synthesis of Nand Laboratory	omaterials	0	0	3	2	50	50	100
		Total	18	3	3	23		700	
		Semes							
Course Code	Cours	se Name	Ho	urs/ W	eek	Credit	Ma	aximum	Marks
	Cours	se ivallie	L	Т	Р	С	CA	ES	Total
THEORY									
10 PNT 201		terisation Techniques	3	1	0	4	50	50	100
10 PNT 202	Nanomaterials an		3	0	0	3	50	50	100
10 PNT 203	Industrial Nanoted	hnology	3	0	0	3	50	50	100
10 PNT 204	Nanoelectronics		3	1	0	4	50	50	100
10 PNT 205	Nanolithography		3	0	0	3	50	50	100
10 PNT 206	Nanobiotechnolog	у	3	0	0	3	50	50	100
PRACTICAL			ı				,		
10 PNT 207	Characterisation of Laboratory		0	0	3	2	50	50	100
10 PNT 208	Technical Report I Presentation	Preparation and	0	0	2	0	100	00	100
		Total	18	2	5	22		800	

	K.S. Ranga	samy College of Tech	nolog	y, Tirı	uchen	gode 637 2	:15		
	Curricul	um for the programmes	unde	r Autoi	nomou	s Scheme			
Regulation	R 2010								
Department		Department of Nanos	cience	and T	echno	logy			
Programme Co	ode & Name	PNT: M.Tech. Nanos	cience	and T	echnol	ogy			
		Semes	ter III						
0	0	Na	Ho	urs/ W	eek	Credit	Ma	aximum l	Marks
Course Code	Cour	se Name	L	Т	Р	С	CA	ES	Total
THEORY				,	,		•		
10 PNT 301	Nanodevices		3	0	0	3	50	50	100
10 PNT E1*	Elective I		3	0	0	3	50	50	100
10 PNT E2*	Elective II		3	0	0	3	50	50	100
PRACTICAL							•		
10 PNT 302	Project Work - Ph	ase I	0	0	12	2	100	00	100
		Total	9	0	12	11		400	
		Semes	ter IV				•		
Carrage Carda	0	Nove	Но	urs/ W	eek	Credit	Ma	aximum l	Marks
Course Code	Course Name		L	Т	Р	С	CA	ES	Total
10 PNT 401	Project Work - Ph	ase II	0	0	40	10	50	50	100
Total			0	0	40	10		100	

K.S. Rangasamy College of Technology, Tiruchengode 637 215									
	Curricul	um for the programmes	s unde	r Autor	nomou	s Scheme			
Regulation	Regulation R 2010								
Department		Department of Nanos	cience	and T	echno	logy			
Programme Co	ode & Name	PNT: M.Tech. Nanos	cience	and T	echnol	ogy			
		Electi	ive I						
Course Code	Cour	se Name	Ηοι	ırs / W	eek	Credit	Ma	aximum	Marks
Course Code	Cour	se name	L	Т	Ρ	С	CA	ES	Total
10 PNT E11	Micro Electro Med Nano Electro Med	hanical System and hanical System	3	0	0	3	50	50	100
10 PNT E12	Drug Delivery		3	0	0	3	50	50	100
10 PNT E13	Fundamentals of I	Batteries	3	0	0	3	50	50	100
10 PNT E14	Nanotechnology in	n polymers	3	0	0	3	50	50	100
10 PNT E15	Solid state of Nan	otechnology	3	0	0	3	50	50	100
10 PNT E16	Nanotechnology in devices	n semiconductor	3	0	0	3	50	50	100
		Electi	ve II						
10 PNT E21	Nanosafety and E	nvironmental Issues	3	0	0	3	50	50	100
10 PNT E22	Intellectual Property Rights		3	0	0	3	50	50	100
10 PNT E23	Research Methodology - Engineering and Management Studies		3	0	0	3	50	50	100
10 PNT E24	Research Method Humanities	ology - Science and	3	0	0	3	50	50	100

	K. S. R	angasamy College of Technol	ogy -	<u>Auton</u> o	mous l	Regul			R 20								
Dei	partment	Nanoscience and Technology	Pro	gramme		k	PNT : M.			ice and							
			S-0	Nam mester				Techno	ology								
		T	<u> </u>														
Cou	ırse Code	Course Name		Hou	rs / We		Credit	Maximum Marks									
				L	Т	Р	С	CA	ES	Total							
10	PNT 101	APPLIED NUMERICAL METHODS	1 3 1 1 1 1 4						50	100							
Ob	jective(s)	With the present development of the computer technology, it is necessary to develop efficing algorithms for solving problems in science, engineering and technology. This course give complete procedure for solving different kinds of problems that occur in engineer numerically. At the end of the course the students would be acquainted with the basic concern numerical methods and their uses.								se gives a							
1	SOLUTIO	N OF EQUATION				To	tal Hrs		09								
		od - Newton Raphsan method-	Metho	od of Fa	lse Pos	sition,	Iteration M	ethod, S	Secant M	ethod and							
2	SOLUTIO	N OF EQUATION AND EIGEN \	/ALU	E PROB	LEM	To	tal Hrs		09								
- Se	eidal iteratio liagonal Ma	ear Systems: Matrix Inversion Me on Method, Solution of Tridiagon trix, Householder Method, QR M	al Sys ethod	tems, E													
3	DIFFERE	ALUE PROBLEMS FOR ORDIN NTIAL EQUATIONS					tal Hrs		09								
Met		od of Successive approximation order only). Boundary-Value lesses.															
4		RY VALUE PROBLEMS FOR O DIFFERENTIAL EQUATIONS	RDINA	ARY AN	D	То	tal Hrs		09								
			obi's	Method	, Gaus	s-Seid	lal Method	d- ADI	method,	Poisson Equation - Laplace's Equation: Jacobi's Method, Gauss-Seidal Method- ADI method, Parabolic							
5	NUMERIO	CAL INTEGRATIONS		Equations, and Hyperbolic Equations.													
5 NUMERICAL INTEGRATIONS Total Hrs 09 Numerical integrations by Trapezoidal and Simpson's 1/3 and 3/8 rules, Two and three point Gaussian quadrature formulas, Romberg's Method- Double intergrades using trapezoidal and Simposon's rules. Finite							tal Hrs		09	Paraboli							
qua	drature for	egrations by Trapezoidal and S mulas, Romberg's Method- Dou	ıble in	itergrade	and 3	3/8 ru	es, Two	and thre	e point	Gaussiar							
qua Elei	drature for ment Metho	egrations by Trapezoidal and S mulas, Romberg's Method- Dou od-Rayleigh-Ritz Method, Galerki	ıble in	itergrade	and 3	3/8 ru	es, Two	and thre d Simpo	e point	Gaussiar							
qua Elei Tota	drature for ment Metho al hours to	egrations by Trapezoidal and S mulas, Romberg's Method- Dou od-Rayleigh-Ritz Method, Galerki	ıble in	itergrade	and 3	3/8 ru	es, Two	and thre	ee point oson's ru	Gaussia							
qua Elei Tota Ref	drature for ment Metho al hours to erence(s):	egrations by Trapezoidal and S mulas, Romberg's Method- Dou od-Rayleigh-Ritz Method, Galerki be taught	ible in	tergrade	es usin	3/8 ru g trap	es, Two a	d Simpo	ee point oson's ru 45	Gaussia							
qua Elei Tota	drature for ment Methodal hours to erence(s): S.S. Sast M.K. Jair Internatio	egrations by Trapezoidal and Smulas, Romberg's Method- Doubd-Rayleigh-Ritz Method, Galerking to taught ry, "Introductory Methods of Numa, S.R.K. Iyenkar and R.K. Janal Limited Wiley Eastern Limited	n Met nerical in, "Net	Analysi Jumerica	s", Prer al Meth	3/8 ru g trap	es, Two sezoidal an	a, PVT. L	ee point pson's ru 45 TD, lutions",	Gaussia les. Finit							
qua Elei Tota Ref	drature for ment Methodal hours to erence(s): S.S. Sast M.K. Jair Internatio P. Kanda Delhi, 200	egrations by Trapezoidal and Smulas, Romberg's Method- Double-Rayleigh-Ritz Method, Galerking to taught ry, "Introductory Methods of Number, S.R.K. Iyenkar and R.K. Janal Limited Wiley Eastern Limited samy, K.Thilakavathy and Gun 25.	n Met nerical in, "Nev avath	Analysi lumerica v Delhi, y "Nume	s", Prer al Meth 1995. erical N	8/8 rug trap	es, Two sezoidal and lall of India Problems	a, PVT. Land Sol	ee point pson's ru 45 TD, lutions",	Gaussia les. Finit New Ag							
qua Elei Tota Ref 1 2	drature for ment Methodal hours to erence(s): S.S. Sast M.K. Jair Internatio P. Kanda Delhi, 200 B.S. Grey Khanna F	egrations by Trapezoidal and Smulas, Romberg's Method- Doubd-Rayleigh-Ritz Method, Galerkin be taught ry, "Introductory Methods of Number, S.R.K. Iyenkar and R.K. Janal Limited Wiley Eastern Limited samy, K.Thilakavathy and Gun 105. val, "Numerical Methods in Englublishers, New Delhi, 2003.	nerical in, "Ned in, "Ned, Nev avath	Analysi Jumerica v Delhi, y "Nume	s", Preral Meth 1995. erical M	3/8 ru g trap ntice-H lods f	es, Two sezoidal and lall of India Problems Is" S. Cha	a, PVT. Land Soland & Con FORT	ee point pson's ru 45 TD, lutions", company	Gaussia les. Finit New Ag							
qua Elei Tota Ref 1 2	drature for ment Methodal hours to erence(s): S.S. Sast M.K. Jair Internatio P. Kanda Delhi, 200 B.S. Grey Khanna F	egrations by Trapezoidal and Smulas, Romberg's Method- Doubd-Rayleigh-Ritz Method, Galerkine taught ry, "Introductory Methods of Number, S.R.K. Iyenkar and R.K. Janal Limited Wiley Eastern Limited samy, K.Thilakavathy and Gun 195. val, "Numerical Methods in Eng	nerical in, "Ned, New avath	Analysi Jumerica v Delhi, y "Nume ng & So	s", Preral Methodology Methodo	3/8 rug trap	es, Two sezoidal and lall of India Problems Is" S. Charrograms in	a, PVT. Land Soland & Con FORT	ee point pson's ru 45 TD, lutions", lutions", Company AN 77, Company	Gaussia les. Finit New Ag Ltd, Nev							

OPNT 102 QUANTUM CONCEPTS 3 1 0 4 50 50 100	K.S. R	angasamy College of Ted	hnology -	- Autono	mous	Regul	ation		R 20	10
Semester Semester Course Code Course Name Hours / Week Credit Maximum Marks L T P C CA ES Total 10 PNT 102 QUANTUM CONCEPTS 3 1 1 0 4 5 0 5 0 5 0 100 Dipart the basic knowledge about the Quantum Concepts and understand the various parameters like operator, Eigen function, angular momentum, the variation principles are approximate methods. Understand the quantum concept and apply the nanostructure materials. 1 INTRODUCTION Total Hrs 9 Possible Concept and paper of the particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. Total Hrs 9 Possible Concept and paper Postulates of quantum of particle - Hermitian operator - Linear harmonic oscillator - Operator method - Postulates of quantum mechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matricepresentation of wave functions. Total Hrs 9 Possible Community Possib	Department		Progra		ode &		PNT : M.			ce and
Course Code Course Name Hours / Week Credit Maximum Marks L T P C CA ES Total 10 PNT 102 QUANTUM CONCEPTS 3 1 1 0 4 50 50 100 Impart the basic knowledge about the Quantum Concepts and understand the variou parameters like operator, Eigen function, angular momentum, the variation principles are approximate methods. Understand the quantum concept and apply the nanostructure materials. INTRODUCTION Total Hrs 9 Limitation of classical mechanics - Plank's quantum hypothesis - Einstein's photoelectric effect - Wave nature of particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. WAVE MECHANICS Invertigation of classical mechanics - Plank's quantum hypothesis - Einstein's photoelectric effect - Wave nature of particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. WAVE MECHANICS Invertigation - Postulates of quantum echanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matricepresentation of wave functions. OPERATORS AND COMPUTATION LAWS Total Hrs 9 Linear momentum operator - Properties of Hermition operator - Angular momentum operators - Ladd operators - Parity operator - Commutation relation L, and L, a		reclinology	9		1			reciiii	Jiogy	
Course Code Course Name L T P C CA ES Total 10 PNT 102 QUANTUM CONCEPTS Impart the basic knowledge about the Quantum Concepts and understand the variou parameters like operator, Eigen function, angular momentum, the variation principles an approximate methods. Understand the quantum concept and apply the nanostructure materials. INTRODUCTION IN				1		ok	Cradit	N/1	ovimum N	Aorko
Impart the basic knowledge about the Quantum Concepts and understand the variou parameters like operator, Eigen function, angular momentum, the variation principles are approximate methods. Understand the quantum concept and apply the nanostructure materials. 1 INTRODUCTION	Course Code	Course Name								Total
Objective(s) parameters like operator, Eigen function, angular momentum, the variation principles are approximate methods. Understand the quantum concept and apply the nanostructure materials. 1 INTRODUCTION Total Hrs 9 Limitation of classical mechanics - Plank's quantum hypothesis - Einstein's photoelectric effect - Wave nature of particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. Total Hrs 9 Linear operator - Hermitian operator - Linear harmonic oscillator - Operator method - Postulates of quantum mechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Mattrepresentation of wave functions. Total Hrs 9 Linear momentum operator - Properties of Hermition operator - Angular momentum operators - Parity operator - Commutation relation L₂ and L₂ - Commutation relation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation - Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation - Charge and current densities - Inadequacies of Klein-Gordon equation - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatre-Fock equation. 45 Total hours to be taught 45 Referenc	10 PNT 102	QUANTUM CONCEPTS		3	1	0	4	50	50	100
Limitation of classical mechanics - Plank's quantum hypothesis - Einstein's photoelectric effect - Wave nature of particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. 2 WAVE MECHANICS Total Hrs 9 Linear operator - Hermitian operator - Linear harmonic oscillator - Operator method - Postulates of quantum mechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matricepresentation of wave functions. 3 OPERATORS AND COMPUTATION LAWS Total Hrs 9 Linear momentum operator - Properties of Hermition operator - Angular momentum operators - Ladd operators - Parity operator - Commuting and non commuting operators - Commutation relation L _x and L _y . 4 VARIATION PRINCIPLES Total Hrs 9 Variation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation - Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation - Charge and current densities - Inadequacies of Klein-Gordon equation - Dirac equation for a free particle - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	Objective(s)	approximate methods. Orderstand the quantum concept and apply the handstructured								
of particle - Uncertainty principle - Schrodinger's time dependent and independent wave equations - Particle a one dimensional box - Harmonic oscillator. 2 WAVE MECHANICS Total Hrs 9 Linear operator - Hermitian operator - Linear harmonic oscillator - Operator method — Postulates of quantumechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matricepresentation of wave functions. 3 OPERATORS AND COMPUTATION LAWS Total Hrs 9 Linear momentum operator — Properties of Hermition operator — Angular momentum operators — Ladd operators — Parity operator — Commuting and non commuting operators — Commutation relation L _x and L _y Commutation relation L ² and L _x — Commutation relation L _y and L _y — Total Hrs 9 Variation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation — Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation — Charge and current densities — Inadequacies of Klein-Gordon equation — Dirac equation for a free particle - Dirac's matrices — Properties of Dirac's matrices — Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	1 INTRODU	JCTION				To	tal Hrs		9	
Linear operator - Hermitian operator - Linear harmonic oscillator - Operator method - Postulates of quantum mechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matrepresentation of wave functions. 3 OPERATORS AND COMPUTATION LAWS	of particle - Ur	ncertainty principle - Schroo	dinger's tim							
mechanics - Equations in motion - Ehren fast's theorem - Hydrogen atom - Hydrogen orbitals - Matricepresentation of wave functions. 3	2 WAVE M	ECHANICS				To	tal Hrs		9	
Linear momentum operator – Properties of Hermition operator – Angular momentum operators – Ladd operators – Parity operator – Commuting and non commuting operators – Commutation relation L _x and L _y Commutation relation L ² and L _x – Commutation relation L ₊ and L. 4 VARIATION PRINCIPLES Total Hrs 9 Variation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation – Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation – Charge and current densities – Inadequacies of Klein-Gordon equation – Dirac equation for a free particle - Dirac's matrices – Properties of Dirac's matrices – Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	mechanics - representation	Equations in motion - Eh of wave functions.	ren fast's			droger	atom - F		n orbitals	
operators - Parity operator - Commuting and non commuting operators - Commutation relation L _x and L _y Commutation relation L ² and L _x - Commutation relation L ₊ and L. 4 VARIATION PRINCIPLES Total Hrs 9 Variation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation - Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation - Charge and current densities - Inadequacies of Klein-Gordon equation - Dirac equation for a free particle - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	-			ition on	orotor			ntum o		Loddor
VARIATION PRINCIPLES Variation principle - Variation method for ground state of hydrogen molecule - Ground state of Helium atom Perturbation theory in non-degenerate case - First order perturbation - Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation - Charge and current densities - Inadequacies of Klein-Gordon equation - Dirac equation for a free particle - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	operators - Pa	arity operator – Commutin	g and non	commu	itina op					
Perturbation theory in non-degenerate case - First order perturbation - Harmonic perturbation - Transition continuous states. 5 APPROXIMATION METHODS Total Hrs 9 Klein-Gordon equation - Charge and current densities - Inadequacies of Klein-Gordon equation - Dirac equation for a free particle - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.						To	tal Hrs		9	
Klein-Gordon equation – Charge and current densities – Inadequacies of Klein-Gordon equation – Dirac equation for a free particle - Dirac's matrices – Properties of Dirac's matrices – Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	Perturbation th	neory in non-degenerate ca	ground sta ase - First	ate of hy order p	/droger erturba	mole tion –	cule - Grou Harmonic	ind state perturba	e of Heliu tion - Tra	m atom – ansition to
equation for a free particle - Dirac's matrices - Properties of Dirac's matrices - Negative energy states Hatree-Fock equation. Total hours to be taught 45 Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	5 APPROX	IMATION METHODS				To	tal Hrs		9	
Reference(s): 1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. 2 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. 3 L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	equation for a	lein-Gordon equation – Charge and current densities – Inadequacies of Klein-Gordon equation – Dirac's quation for a free particle - Dirac's matrices – Properties of Dirac's matrices – Negative energy states – latree-Fock equation								
G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004. B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	Total hours to	be taught							45	
 B.M. Mathew and K. Venkateshan, "A Text Book Quantum Mechanics", Tata McGraw Hill publication New Delhi, 2007. L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968. 	Reference(s):									
New Delhi, 2007. L.I. Schiff, "Quantum Mechanics", McGraw Hill book company 1968.	1 G. Aruldhass, "Quantum Mechanics", Prentice Hall of India pvt. Ltd. New Delhi, 2004.									
	New Dell	New Delhi, 2007.								
4 Ghatak and Lokanathan "Quantum Mechanics". The Macmillan Company of India Ltd 1975.										
The state of the s	4 Ghatak a	nd Lokanathan "Quantum N	Mechanics'	', The M	acmilla	n Com	pany of Ind	lia Ltd 19	975.	
5 Amit Goswami, "Quantum Mechanics", WCB publishers, 1992.	5 Amit Gos	wami, "Quantum Mechanic	s", WCB p	ublisher	s, 1992					

K.S. R	angasamy College of	f Technology -	Auton	omous	Regul	ation		R 20	10
Department	Nanoscience and Technology	Programme	Code 8	& Name	,	PNT : M.	Tech - N Techno	anoscien ology	ce and
		S	emeste	r I					
Course Code	Course Na	ama	Hot	urs / We	eek	Credit	Maximum Marks		
Course Code			L	Т	Р	С	CA	ES	Total
10 PNT 103	INTRODUCTION TO SCIENCE AND TEC	CHNOLOGY	3	0	0	3	50	50	100
Impart the basic knowledge on nanoscience and technology. Understand the various process techniques available for the processing of nanostructured materials. Impart knowledge on the exotic properties of nanostructured materials at their nanoscale lengths. Acquire the knowledge above the various nanoparticles process methods and their skills. Study the reactive merits of various process techniques.									
1 INTROE	DUCTION				То	tal Hrs		9	
	nanoscale materials - f nanoscience and tecl		cular si	ze. Scie	entific r	evolutions	-nanoted	chnology	application
	TRUCTURES AND DI					tal Hrs		9	
	of nanostructures-zer s-quantum size effects							ize Depe	endency in
	IATERIAL SYNTHESIS					tal Hrs		9	
	nanomaterials-top dow nesis-mechanical grind				Metho	d of nano	materials	prepara	tion – wet
_	ATERIAL PROPERTIE	_				tal Hrs		9	
	ume ratio. Surface pro properties of nanom								
5 PHYSIC MATER	AL PROPERTIES OF IALS	NANOSTRUC	TURED		Tot	tal Hrs		9	
	s-optical properties an avior of nanomaterial								
Total hours to	be taught							45	
Reference(s)									
Mick Wilson, Kamali Kannargare., Geoff Smith, "Nano technology: Basic Science and Emerging technologies", Overseas Press, 2005.									
2 Charles P. Poole, Frank J. Owens, "Introduction to Nanotechnology", Wiley Interscience, 2003.									
Mark A. Ratner, Daniel Ratner, "Nanotechnology: A gentle introduction to the next Big Idea", Prentice Hall P7R:1 st Edition, 2002.									
	_								
4 T. Prade	eep, " Nano the Essent H. Hoffmann, "Nanom				hnolog	y", Tata M	cGraw hi	II, 2007.	

	K.S. Rangasamy College of Technology - Autonomous Regulation R 2010									
De	partment	Nanoscience and Technology	Programm	e Code 8	& Name		PNT : M	Tech - N. Techn	lanoscien ology	nce and
		<u> </u>		Semeste	er I	•				
0	0	Causa a Na		Hou	rs / Wee	k	Credit	М	aximum N	Marks
Cot	ırse Code	Course Na	ime	L	Т	Р	С	CA	ES	Total
10	PNT 104	ADVANCED MATE TECHNOLOGY	1	0	4	50	50	100		
Ob	jective(s)	Understand the b properties and value material.etc. Impairmemory alloys and	arious applicated the knowle acquire the v	ations o dge abo	of dielec out the r	tric r new r	naterials naterials I	magneti ike sma	c, supero	conducting als, shape
1		JRE & BONDS OF S					tal Hrs		9	
bond lattic cente	ds-Dispersic e-basis - cr ered-Face	ds-lonic bonding-bor on bonds-dipole bond rystal structure-unit of centered -hexagon Fresnel defect-Line in	ds-hydrogen b cell-Lattice Pa al-crystal syr	oonds – rameter- mmetry-N	propertie Primitiv Miller in	es - si e cell dices.	tructure of crystal sy Imperfe	solids-L stems - ction-Poi	attice Po simple cu nt defec	ints-Space ubic - body
2	DIELECTF	RIC MATERIALS				Tot	tal Hrs		9	
elect Diele Dipo	ricity-Piezo ectric Loss - lar relaxatio	rials: Basic concepts electricity-Properties - Ionic polarizability a on - Effects of Dielect	of Dielectric s a function o	in alterr of freque	nating fie	elds- iplex	The comp dielectric o	lex Diele	ectric Cor of Non-po	nstant and
3		C MATERIALS					tal Hrs		9	
	eptibility of		Magnetic materials: Dia and Paramagnetic materials-Quantum theory of paramagnetic materials-Paramagnetic susceptibility of conduction electrons-Ferroids.							
SEMI CONDUCTING & SUPERCONDUCTING Total Hrs.								ı	Criais-i ai	ramagnetic
	MATERIAL	_S	RCONDUCTI						9	
Sem quar	MATERIAL iconducting		RCONDUCTING ductor-Direct	and Indir		l gap	characteri	stics-Qu	9 antum co	nfinement-
Sem quar	MATERIAL iconducting tum dots	_S materials: Semicon and wires-organic	RCONDUCTING ductor-Direct	and Indir		l gap nicon	characteri	stics-Qu	9 antum co	nfinement-
Sem quar appli 5 New	MATERIAL iconducting atum dots ications. NEW MAT Materials:	_S materials: Semicon and wires-organic	ductor-Direct semiconduct	and Indir ors-Poly alloys-s	mer ser	I gap micon Tot	characteri ductors-P tal Hrs	stics-Qu hoto co	9 antum co nductive 9	nfinement- polymers-
Sem quar appli 5 New funct	MATERIAL iconducting atum dots ications. NEW MAT Materials:	materials: Semicond and wires-organic ERIALS Smart materials-shorties-processing-text	ductor-Direct semiconduct	and Indir ors-Poly alloys-s	mer ser	I gap micon Tot	characteri ductors-P tal Hrs	stics-Qu hoto co	9 antum co nductive 9	nfinement- polymers-
Sem quar appli 5 New funct	MATERIAL iconducting ntum dots ications. NEW MAT Materials: tional prope	materials: Semicond and wires-organic ERIALS Smart materials-shorties-processing-text	ductor-Direct semiconduct	and Indir ors-Poly alloys-s	mer ser	I gap micon Tot	characteri ductors-P tal Hrs	stics-Qu hoto co	9 antum co nductive 9 tic Tran	nfinement- polymers-
Sem quar appli 5 New funct	MATERIAL iconducting ntum dots ications. NEW MAT Materials: tional proper I hours to be rence(s):	materials: Semicond and wires-organic ERIALS Smart materials-shorties-processing-text	ductor-Direct semiconduct ape memory ure applicatio	and Indir ors-Poly alloys-s ns.	mer ser	I gap micon Tot emory	characteri ductors-P tal Hrs r effects-	stics-Qu hoto co	9 antum co nductive 9 tic Tran	nfinement- polymers-
Sem quar appli 5 New funct Tota	MATERIAL iconducting itum dots ications. NEW MAT Materials: tional prope I hours to be erence(s): V. Rajendr	materials: Semicond and wires-organic ERIALS Smart materials-shorties-processing-text e taught	ductor-Direct semiconduct ape memory ure applicatio , Tata McGra	and Indir ors-Poly alloys-s ns.	mer ser	I gap micon Tot emory 2011	characteri ductors-Pl tal Hrs / effects-	stics-Qu hoto co	9 antum co nductive 9 tic Tran	nfinement- polymers-
Sem quar appli 5 New funct Tota Refe	MATERIAL iconducting itum dots ications. NEW MAT Materials: tional prope I hours to be erence(s): V. Rajendr A.J. Dekke	materials: Semicono and wires-organic ERIALS Smart materials-sharties-processing-text te taught an, Material Science er, Solid state Physics, Solid state Physics,	ductor-Direct semiconduct ape memory ure applicatio , Tata McGras, Macmillan I	and Indir ors-Poly alloys-s ns. w Hill, Ne ndia Ltd,	hape me	Totemory 2011 Ship 20	characteri ductors-Pl tal Hrs / effects- l. 012. Revised Ed	stics-Quinoto con Martens	9 antum co nductive 9 tic Tran	nfinement- polymers-
Sem quar appli 5 New funct Tota Refe	MATERIAL iconducting itum dots ications. NEW MAT Materials: tional prope I hours to be erence(s): V. Rajendr A.J. Dekke	materials: Semicono and wires-organic ERIALS Smart materials-shorties-processing-texte taught an, Material Science or, Solid state Physical	ductor-Direct semiconduct ape memory ure applicatio , Tata McGras, Macmillan I	and Indir ors-Poly alloys-s ns. w Hill, Ne ndia Ltd,	hape me	Totemory 2011 Ship 20	characteri ductors-Pl tal Hrs / effects- l. 012. Revised Ed	stics-Quinoto con Martens	9 antum co nductive 9 tic Tran	nfinement- polymers-

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Departm	ent	Nanoscience and Technology	Programme Co	de &	Name		PNT : M.	Tech - N Techn		nce and
			Semes	ter I						
Course (Codo	Course N	lamo	Н	ours / V	Veek	Credit	Ma	aximum I	Marks
Course	Jude	Course N	lame	L	T	Р	С	CA	ES	Total
10 PNT	105	INTRODUCTION TO		3	0	0	3	50	50	100
Objectiv	Understand the basic properties of biomaterials and the classes of biomaterials implant, knowledge about DNA nanotechnology and nanosensors and understand basic Characterisation techniques related to DNA Nanotechnology. Understand the applications of biomaterials for implant applications.									
1 INTI	RODUC	CTION				To	tal Hrs		9	
character	istics-	nd biological material naturally occurring biom	aterials- pure met			eramic	s-polymer		sites.	s-General
		GENERATION BIOMAT					al Hrs		9	
Second (tion bio materials and t gels.	their properties - I	Bioac	tive ar	nd biod	degradabl	e ceran	nics-biod	egradable
		NERATION BIOMATER					al Hrs		9	
conjugate	es-micr	n biomaterials - Charad o array technologies- ials - molecular machine	Micro-nanotechno							
1 1		NGINEERING					al Hrs		9	
structure tissue en	and ful gineeri	r and Tissue Engineeri nction of natural extrace ing – Top-down and b – Self-assembly - Futur	ellular matrix – App ottom-up approac	olicat	ion of r	nanote	chnology	in devel	oping sc	affolds for
5 DNA	A TECH	INOLOGY				Tot	al Hrs		9	
Introduction-DNA nanotechnology-structural DNA assembly – DNA nano pore - arrays- DNA detection, sorting, sequencing- DNA studies by AFM - DNA computer - PCR amplification of DNA fragments-Molecular surgery of DNA - nanoscale organization-characterization-quantum size effects – nano-biosensors.										
Total hou	rs to be	e taught							45	
Reference(s):										
1 Raplph et al, "Nanoscale Technology in Biological Systems", CRC Press, 2005.										
Verl	ag GM	yer & C.A. Mirkin, "Nar BH & Co, 2004.							ctives", W	/iley VCH
		rk, R.S. Lakes, "Bio Ma								
	4 Challa Kumar (Ed.) "Tissue, cell and Organ Engineering", Nanotechnologies for life sciences, Wiley VCH 2009									

K	(.S. Ra	angasamy College of T	echnology - Au	itonom	ous R	egulat	ion		R 20)10
Departm	nent	Nanoscience and Technology	Programme (Code &	Name		PNT : M.	Tech - N Techn		nce and
			Seme	ster I						
0	\	Oarmaa Na		Hou	Hours / Week		Credit	Ma	aximum I	Marks
Course C	Joue	Course Na	me	L	Т	Р	С	CA	ES	Total
10 PNT ²	106	COMPUTER PROGRA AND C++		3	0	0	3	50	50	100
Objective((s)	Impart the basic progra	mming in C & C	++.						
1 BAS	IC CO	NCEPTS IN C				То	tal Hrs		9	
Output –	Contro	Keywords - Constant V ol Structures – if and Sv cter strings – Simple pro	vitch statements							
2 FUN	ICTIO	N & POINTERS				To	tal Hrs		9	
		unctions - Defining and inter Declarations – Pas							tions pro	ototypes -
3 STR	UCTU	RE & ARRAYS				To	tal Hrs		9	
		ata types - Structures - sequential file processi					g membe	rs – Ar	ay of sti	ructures –
4 BAS	IC CO	NCEPTS IN C++				To	tal Hrs		9	
declaratio	on – D	Programming (OOP) - Differences between C jects – Constructors and	and C++ - Fun	ctions	in C++	Fu	nction ov	erloadir	g/polymo	–variable orphism –
5 TYPI	ES OF	CLASSES				To	tal Hrs		9	
		ses - Inheritance and ects and derived classes			el, mul	tilevel,	multiple	and hy	brid inhe	eritance –
Total hour	rs to b	e taught							45	
Reference	Reference(s):									
1 E. Ba	1 E. Balagurusamy, "Object – Oriented Programming with C++", Tata McGraw – Hill									
2 Robe	ert Laf	ore, "Object-Oriented Pr	ogramming in T	urbo C	++" , G	algotia	Publicati	ons,199	5	
3 W. K India	_	nan Brain and M. Ritchi	e Dennis, "The C	C Prog	rammin	g Lan	guage", 2	nd Editio	n, Prent	ice Hall of
4 Bjarr	Bjarne Stroustrup, "Programming: Principles and practice using C++, Addison-Wesley professional.									

K.S. Ra	K.S. Rangasamy College of Technology - Autonomous Regulation R 2010								
Department	Nanoscience and Technology	Programme Code & Name PNT : M.Tech - Nanoscience a			e and				
		Semeste	er I						
Course Code	Course	Nama	Hours / Week			Credit	Maximum Marks		larks
Course Code	Course	Name	L	Т	Р	С	CA	ES	Total
10 PNT 107	SYNTHESIS OF NAN LABORATORY	IOMATERIALS	0	0	3	2	50	50	100
Objective(s) Understand the different methods to prepare the nanoparticles and technical skill on the process method.									

- 1. Preparation of nanoparticles chemical reduction
- 2. Preparation of nanoparticles sol-gel
- 3. Preparation of nanoparticles sonochemical
- 4. Preparation of nanoparticles ball milling
- 5. Preparation of nanoparticles spray pyrolysis
- 6. Preparation of nanocomposite materials
- 7. Nanocrystalline thin film by spin coating
- 8. Chemical bath deposition by dip coating

Total Hrs	45
TOTALLIS	45

Ī	K.S. Ran	gasamy College of Te	echnology - Autono	mous	Regula	ation			R 2010)
Depa	artment	Nanoscience and Technology	Programme Coo Name	le &		PNT	: M.Tech Te	n - Nan chnolo		e and
			Semeste	er II						
Courc	se Code	Course	Nama	Hou	rs / We	ek	Credit	М	aximum	Marks
Cours	se Code	Course	name	L	Τ	Р	С	CA	ES	Total
10 PI	NT 201	ADVANCED CHARA TECHNIQUES	CTERISATION	3	1	0	4	50	50	100
Objective(s) Understand the relative methods of various characterisation techniques and the basic knowledge about the different characterisation techniques. Impart the knowledge about the characterisation techniques and study each and every technique and acquire the knowledge to use the technique.										
1 N	MICROSO	COPY				То	tal Hrs		9	
electro	on microstion in el	tion and emission spe scopy – Transmission ectron microscopes – ut the nanometer scale	electron microscopy Environmental trans	– Sca missio	inning n elect	tunne tron m	ling elect	tron mi y – Ele	croscop	y – Image
		IG PROBE MICROSCO					tal Hrs		9	
Optica (SIMS	al micros	e microscopy – Atomic copy – Confocal micro metry – Matrix assisted DSCOPY	oscopy – Scanning r	near fie	eld opt	ical m	nicroscop	y – Se	condary	
spectr spectr	roscopy - roscopy -	of semiconductors – Ex - Dynamic Light Scat - Thermo gravimetric alysis (TMA).	tering (DLS) - NMF	R Spec	ctrosco	ру –	ESR spe	ectrosc	opy – N	/lossbauer
		ICAL CHARACTERISA	ATION			То	tal Hrs		9	
hardn	ess – Fa	naracterization – Modi tigue – Abrasion and v e – Surface Force app	wear resistance – Ši	per pla	asticity	– Na	ino inden	tation -	- Nano i	tribology –
5 5	STRUCT	JRAL CHARACTERIZA	ATION			То	tal Hrs		9	
crysta - The	allography ermo lumi	X- ray diffraction — vusing synchrotron rac nescence — X-ray abso ctron scattering for che	liation – Role for neu orption Fine Structure	itron so e (XAF	atterin	ig in r	ano sciei	nce - P	hotolum	inescence
	hours to b								45	
Refere	ence(s):									
1 T	T.Pradeer	o, "Nano: The Essentia	ls", Tata McGraw Hil	I, New	Delhi,	2007.				
2 (Charles P	Poole Jr and Frank J	Ownes, "Introduction	to Nan	otechr	nology	/", John V	Viley So	ns, 200	3.
2 (an Kamali Kamanan	ro Cooff Smith Mi	chelle	Simmo	ons. E	Burkar Ra	aguse.	"Nanote	chnology:
3 1		son, Kamali Kannanga ences and emerging tec								ciliology.
3 N	Basic scie		chnologies", Oversea	s Pres	s, 2005	5.				

K.S. Rai	ngasamy College of Tec				Regul	ation		R 2	010
Department	Nanoscience and	Program		ode &		PNT : M	.Tech - N		nce and
2 0 0 0 1 1 1 1 1 1 1 1	Technology	l .	lame				Techn	ology	
		S	emest			T	1		
Course Code	Course Nam	۵	Ho	urs / W	eek	Credit	N	laximum	Marks
			L	Т	Р	С	CA	ES	Total
10 PNT 202	NANOMATERIALS AI NANOMEDICINE		3	0	0	3	50	50	100
	Understand the prin								pplication of
Objective(s)	Nanomaterials in med								
Impart the knowledge to apply the Nanomaterials in different medical applications and gain the knowledge for the solution of right nanomaterials for biomedical applications.									
1 BASIC O	F NANOBIOMOLECULE		igni na	momate		tal Hrs	саг арріі	<u>calions.</u> 0	
	perty relationship of Bio		rials.	Nano 3	_		teins an	d Polys	accharides –
	erty relationship of tissue								
	aterials – Polymeric sca								
	derivates – Dextrans – A								
_	OF NANOBIOMOLECULE	-				tal Hrs		9	
	- Development of nano								
	system for oral administra				nasal	administra	tion – Dr	rug syste	em for ocular
	- Nanotechnology in diag	gnostic appii	cation		- -	tal I laa		9	
	HNOLOGY		- (S !		tal Hrs	:		ith historiaal
	 Antibody conjugated in omedical nanoparticles - 								
	legradable polymers – Ap		3 2	CHAINIC	,10	Dinordin t	ypcs or	arag loc	ding Drug
	O PARTICLES				То	tal Hrs		9	
Gold and Silve	er nanoparticles in cancer	targeting ar	nd trea	tment -	- Nano	particles i	n treatme	ent of bre	east cancer –
Chemotherapy	y – Active and Passive	cancer tissu	e targ	eting -	Micro	fluidics -	 Chemo 	therape	utic agents -
	y - Vaccine immunother	apy – Radio	therap	y – The	ermoth	nerapy – P	hoto dyn	amic the	erapy – Nano
particulate targ	· · · · · · · · · · · · · · · · · · ·								
	OSENSORS					tal Hrs		9	
	Biosensors – Organizati								
	ر – Surface confined che ر – Raman sensing at sur								
Total hours to		aces - Liec	iio and	aiyticai	SCHSIII	ig – i iasiii	a and op	45	
Reference(s) :								70	
. ,	, "Biomaterials Science a	nd Engineer	ina" E	Danum	Drace	New York	108/		
	ep, "Nano: The essentials		_		1000,	INCAN LOLD	, 1004.		
	s, Dekker, "Encyclopedia	-			tachn	alogy"			
	. Praetories and Tarun K.						/& Formu	ılation	
					וט ווט	ag Deliver)	G I UIIIU	iialiUII	
5 T. Lu, S.	C. Chen, Advanced Drug	Delivery Re	views.						

K.S. Rai	ngasamy College of Tech				Regu	lation		R	2010
Department	Nanoscience and Technology	, and the second	mme Co			PNT :		- Nanos chnology	cience and
			Semeste	er II		T	1		
Course Code	Course Name	2	Hou	rs / We	ek	Credit			m Marks
		,	L	T	Р	С	CA	ES	Total
10 PNT 203	INDUSTRIAL NANOTECHNOLOGY		3	0	0	3	50	50	100
Objective(s)	Understand the applications principles and					stries and	d study	the relat	ive methods o
	NDUCTOR NANOSTRUC				_	tal Hrs			9
	r fabrication techniques. performance of semicond								
	TIC NANOSTRUCTURES					tal Hrs		Ç	9
Fabrication a	solids-magnetic domains and properties of nanc probes. Electronic magne	structured	magn	ets. F	Photoi	nduced	magne	tism an	d spintronics
	NSORS AND ACTUATOR				_	tal Hrs		(
of different na	o electromechanical syste nostructures, advantages mical and mechanical nan	and limita	tions of	variou	s app				
4 MOLECU	LAR ELECTRONICS				To	tal Hrs		Ç	9
Organic electi	nd semiconducting polyr roluminescent displays-inj r order- excimers, H and c	ection, tra	nsport,	excito	n forn	nation an			
5 INDUSTF	RIAL APPLICATIONS				To	tal Hrs		Ç	9
	in bone substitutes & del f nanomaterials. Application								
Total hours to	be taught							4	5
Reference(s):									
1 J. Verdey	en, "Laser Electronics", II	Edition, Pr	entice H	lall, 19	90.				
2 C.W. Turi	ner, T. Van Duzer, "Princip	les of Sup	ercondu	ctive D	Device	s and Cir	cuits", 1	981	
	, M.Pomeranty, "Electro ew York, 1991.	responsive	e molec	ules a	nd po	olymeric	systems	s", Skoth	eim T. Marce
	"Principles of Optical Elec								
⁵ 1995 (ISE	y, M R Bryce, D Bloor (6 BN 0-340-58009-7)	•							
	oannou, P F van Hutten H, 2000 (ISBN 3-527-2950		nducting	Polyr	mers:	Chemistr	y, Phy	sics, and	Engineering
7 D. D. C B	radley, Current Opinion in	Solid State	e & Mate	erials S	Scienc	e Vol. 1,	789 (1 <mark>9</mark>	96)	

Prepared By

K.S. Ran	gasamy College of Tech	nnology -	Autono	mous	Regu	lation		R	2010
Department	Nanoscience and Technology	Progra	amme Co Name	ode &		PNT :		- Nanos chnology	cience and
	-	5	Semeste	r II					
0	O No		Hou	rs / We	ek	Credit		Maximu	m Marks
Course Code	Course Name	!	L	Т	Р	С	CA	ES	Total
10 PNT 204	NANOELECTRONICS		3	1	0	4	50	50	100
Objective(s)	Understand the basic a about the nanostructure nano semiconductor &	ed semico	nducting	g mate	rials.	Ündersta	nd the		
1 BASICS C	F NANOELECTRONICS				То	tal Hrs		Ç	9
Effects on stru Fraction of surf	n solids – diffusion proce cture and Morphology of ace atoms – Specific surf ENDENT PROPERTIES	f free or S	Supporte	d Nan	oparti stress.	cles – S		confine	
Nano level -	nt absorption spectra - Bl AFM, ISTM tip on a sur (quantum wells) - 1 D r clusters -	rface - Ele	ectronic	states	in cı	rystal ene	ergy ba	nds - C	oncepts of 20
3 QUANTU	M SIZE EFFECTS				To	tal Hrs		Ç	9
	antum dots - Coulomb blo quantum dots - Strong a nano defects.								
4 NANOELE	CTRONIC MATERIALS				To	tal Hrs		Ç	9
	Materials Synthesis - Moulsed laser deposition - sputtering.								
5 NANOCO	MPOSITES				To	tal Hrs		Ç	9
nanoparticles -	es - Electronic and atomi - functionalization – Nano- - Switching devices.								
Total hours to b								4	5
Reference(s):									
	nham, Dimitri Vvedensky, ns", Cambridge University			semic	onduc	tor struct	ures: fu	ndamen	tals and device
2 L.Banyai a	and S.W.Koch, "Semicond	ductor Qua	ntum Do	ots", W	orld S	cientific,	1994.		
3 J.H. Davie	es, "An introduction to the	physics-at	low dim	ension	nal ser	niconduct	tors", C	ambridge	Press, 1998.
4 Karl Gose	r, Peter Glosekotter, Jan I	Dienstuhl,	"Nanoel	ectroni	ics an	d Nanosy	stems",	Springe	r, 2004.

K.S. Rar	gasamy College of Tecl	hnology - <i>i</i>	Autono	mous	Regul	ation		R	2010
Department	Nanoscience and Technology		mme Co Name			PNT : I		- Nanos chnology	cience and
		S	emeste	r II					
Course Code	Course Name	,	Hou	rs / We	ek	Credit		Maximu	m Marks
Course Code	Course Marrie	=	L	Т	Р	С	CA	ES	Total
10 PNT 205	NANOLITHOGRAPHY	•	3	0	0	3	50	50	100
Objective(s)	Understand the basic lithography technique industries and study the	s. Impart	knowled	dge ab	out t	he lithog			
1 BASICS II	N LITHOGRAPHY				To	tal Hrs		9	9
nanolithograph nanolithograph					design	for elect		ircuits –	Applications of
	LITHOGRAPHY phy - Light sources - Ph					tal Hrs			9
and negative n	hoto resists – Ultraviolet	lithography	√ — x ra\	/ Litho	araph	v - Proxin	nity brin	ıtına – X	rav masks – X
ray sources – \$ 3 ION BEAN Ion beam litholeam lithograp	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogi	ray projecti am – Point raphy - Ele	source	ray res s of ion	Tot n – lo hy – E	tal Hrs n column Electron o	Beaptics –	m writing Raster s	9 g – Masked ion
ray sources – \$ 3 ION BEAN Ion beam lithograp scan – Electron	Synchrotron radiation – X MLITHOGRAPHY graphy - Focused ion bea	ray projecti am – Point raphy - Ele	source	ray res s of ion	ists. Tot n – Io hy – E	tal Hrs n column Electron o	Beaptics –	m writing Raster s tions.	9 g – Masked ion
ray sources – \$3 ION BEAN Ion beam lithograp scan – Electron 4 MICRO-N Microlithograph Nanolithograph nanolithograph	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogon n proximity / Projection pri	ray projection am - Point raphy - Electing - Electing - Electing - Molecting -	source ctron lith ctron res	s of ionographists – Sesself-as	ists. Tot n – Io hy – E Electro Tot micon sembl	tal Hrs n column Electron o on beam tal Hrs ductor p y – Nano	- Bear ptics - applica rocessiroimprin	m writing Raster s tions. ng – M t lithogra	9 g – Masked ion can and vector 9 EMS design
ray sources – \$3 ION BEAN lon beam lithograph scan – Electror 4 MICRO-N Microlithograph Nanolithograph nanolithograph 5 NANOLIT Tools for nan	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogo proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stere	ray projection am - Point raphy - Electric inting - Electric ersion lithough by - Moleo -lithogra	source: ctron lith ctron res ography lecular : phy - Na	ray res s of ion nograp sists – Se self-as anosca	Tot n – Io hy – E Electro Tot micon semblate 3D	tal Hrs n column Electron o on beam tal Hrs ductor p y – Nano shapes - tal Hrs	– Bea ptics – applica rocessi oimprin - NEMS	m writing Raster s tions. ng – M t lithogra	9 g – Masked ion can and vector 9 EMS design - aphy - Dip-pen
ray sources – \$3 ION BEAM on beam lithograp beam lithograp scan – Electror 4 MICRO-N Microlithograph Nanolithograph 5 NANOLIT Tools for nan- scratching – Re	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogon n proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stero HOGRAPHY TOOLS colithography - Molecular esist and imaging layers.	ray projection am - Point raphy - Electric inting - Electric ersion lithough by - Moleo -lithogra	source: ctron lith ctron res ography lecular : phy - Na	ray res s of ion nograp sists – Se self-as anosca	Tot n – Io hy – E Electro Tot micon semblate 3D	tal Hrs n column Electron o on beam tal Hrs ductor p y – Nano shapes - tal Hrs	– Bea ptics – applica rocessi oimprin - NEMS	m writing Raster s tions. ng – M t lithogra design.	9 g – Masked ion can and vector 9 EMS design - aphy - Dip-pen
ray sources – \$3 ION BEAM on beam lithograp scan – Electror 4 MICRO-N Microlithograph Nanolithograph 5 NANOLIT Tools for nan- scratching – Re Total hours to l	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogon n proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stero HOGRAPHY TOOLS colithography - Molecular esist and imaging layers.	ray projection am - Point raphy - Electric inting - Electric ersion lithough by - Moleo -lithogra	source: ctron lith ctron res ography lecular : phy - Na	ray res s of ion nograp sists – Se self-as anosca	Tot n – Io hy – E Electro Tot micon semblate 3D	tal Hrs n column Electron o on beam tal Hrs ductor p y – Nano shapes - tal Hrs	– Bea ptics – applica rocessi oimprin - NEMS	m writing Raster s tions. ng – M t lithogra design.	9 g – Masked ion can and vector 9 EMS design - aphy - Dip-per 9 thesis – Nanc
ray sources – \$\frac{3}{3} ION BEAN Ion beam lithograph scan – Electron 4 MICRO-N Microlithograph Nanolithograph 5 NANOLIT Tools for nan scratching – Re Total hours to Reference(s) : 1 James R.	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogra n proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stere HOGRAPHY TOOLS colithography - Molecular esist and imaging layers. The provided the second color of the secon	ray projection am — Point raphy - Electric raphy - Electric raphy — Moleo -lithogram manipulate "Microlithogram"	source: ctron lith ctron res ography lecular : phy - Na cion by	s of ionograpsists – Seself-as anosca	Total	tal Hrs n column Electron o on beam tal Hrs ductor p y - Nand shapes - tal Hrs AFM - N	- Bear ptics - applicar rocessi bimpring - NEMS anopati	m writing Raster s tions. ng – M t lithogra design. ern syn RC Pres	9 g – Masked ion can and vector 9 EMS design - aphy - Dip-pen 9 thesis – Nanc 15
ray sources – \$3 ION BEAM lon beam lithograph scan – Electror 4 MICRO-N Microlithograph Nanolithograph nanolithograph 5 NANOLIT Tools for nanscratching – Reference(s): 1 James R. 2 M.Gentili,	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogra proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stere HOGRAPHY TOOLS colithography - Molecular esist and imaging layers. The second seco	ray projection am — Point raphy - Electric raphy - Electric raphy — Moleo -lithogram manipulate "Microlithogram Selci, "N	source: ctron lith ctron res ography ecular : phy - Na cion by	s of ionograpsists – Seself-as anosca	Total	tal Hrs n column Electron o on beam tal Hrs ductor p y - Nand shapes - tal Hrs AFM - N	- Bear ptics - applicar rocessi bimpring - NEMS anopati	m writing Raster s tions. ng – M t lithogra design. ern syn RC Pres	9 g – Masked ion can and vector 9 EMS design - aphy - Dip-pen 9 thesis – Nanc 15
ray sources – S 3 ION BEAN Ion beam lithograph scan – Electror 4 MICRO-N Microlithograph Nanolithograph 5 NANOLIT Tools for nan- scratching – Reference(s): 1 James R. 2 M.Gentili, Ray Lithograph 3 P. Rai-Ch	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogra n proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stere HOGRAPHY TOOLS colithography - Molecular esist and imaging layers. The taught Sheats, Bruce W. Smith, Carlo Giovannella, Stefar graphies", 1st edition, Spri coudhury, "Handbook of m	ray projection am — Point raphy - Electric ersion lithogram — Moleo -lithogram — manipulate — "Microlithogram o Selci, "Nager, 1994 icrolithogram — icrolithog	source: ctron lith ctron res graphy lecular : phy - Ni cion by graphy S lanolitho	ray res s of ion nograp sists – Seself-as anosca STM Science ograph cromae	Tof n – Io hy – E Electro Tof micon semblale 3D Tof and A	tal Hrs n column Electron o on beam tal Hrs ductor p y - Nan shapes - tal Hrs AFM - N	- Bear ptics - applica rocessi pimprin - NEMS anopatt	m writing Raster s tions. ng – M t lithogra design. gern syn RC Pres en STM, ication",	g – Masked ion can and vector general personal p
ray sources – S 3 ION BEAM Ion beam lithograph scan – Electror 4 MICRO-N Microlithograph Nanolithograph 5 NANOLIT Tools for nan- scratching – Reference(s): 1 James R. 2 M.Gentili, Ray Lithograph 3 P. Rai-Ch	Synchrotron radiation – X M LITHOGRAPHY graphy - Focused ion bea hy – Ion projection lithogra n proximity / Projection pri ANO LITHOGRAPHY ny – Microchips - Imme ny - Nanosphere lithogra y - Soft lithography - Stere HOGRAPHY TOOLS colithography - Molecular esist and imaging layers. De taught Sheats, Bruce W. Smith, Carlo Giovannella, Stefar graphies", 1st edition, Spri coudhury, "Handbook of m ner, "Nanotechnology an	ray projection am — Point raphy - Electric ersion lithogram — Moleo -lithogram — manipulate — "Microlithogram o Selci, "Nager, 1994 icrolithogram — icrolithog	source: ctron lith ctron res graphy lecular : phy - Ni cion by graphy S lanolitho	ray res s of ion nograp sists – Seself-as anosca STM Science ograph cromae	Tof n – Io hy – E Electro Tof micon semblale 3D Tof and A	tal Hrs n column Electron o on beam tal Hrs ductor p y - Nan shapes - tal Hrs AFM - N	- Bear ptics - applica rocessi pimprin - NEMS anopatt	m writing Raster s tions. ng – M t lithogra design. gern syn RC Pres en STM, ication",	g – Masked ion can and vector general personal p

	K.S. Ran	gasamy College of Tech	nnology -	Autono	mous	Regul	lation		R	2010
Der	partment	Nanoscience and	Progra	mme co	ode &		PNT : I			cience and
		Technology		Name Semeste	r II			100	chnology	
		1		1	rs / We	ماد	Credit		Maximu	m Marks
Co	urse Code	Course Name)	L	T T	P	Credit	CA	ES	Total
4.0	DNT 200	NANOBIOTECHNOLC	nGV	3	0	•	3		50	100
	PNT 206 piective(s)					0 hnolo		50		
O.	Objective(s) Understand the basic knowledge of Nanobiotechnology and DNA structures. Understand the application of nanomaterials in biotechnology and acquire the knowledge about the DNA, proteins, amino acids, drug delivery, biomedicine etc.,									
1	INTRODU		<u> </u>	•			otal Hrs		Ç	9
Nuc	leis acids	 areas of Biotech and and proteins refinemer materials to basic and ap 	nt and ap	plication						
2	INTERPH.	ASE SYSTEMS				Т	otal Hrs		Ç	9
		tems of devices for medic rics – Introduction – Lipids								
3	PROTEIN	BASED NANOSTRUCTU	JRES			Т	otal Hrs		(9
bior	nolecular r	nanostructures building ecognition events – Natorganic nanoparticles – Natorganic nanoparticles – Natorganic nanoparticles – Natorganic nanoparticles	anobioelec	tronic c						
4		ED NANOSTRUCTURES					otal Hrs			9
		anostructures – Topogr old nanoparticles – DNA								
5		TION OF NANOBIOTECH					otal Hrs		Ç	9
opti		(metal) nanoparticles ar on methods – Nanopartic esticides.								
Tota	al hours to b	e taught							4	5
Ref	erence(s) :									
1	CM, Niem 2004.	eyer, C.A. Mirkin, "Nanob	iotechnolo	gy: Con	cepts,	Applic	cations ar	d Pers	pectives"	, Wiley – VCH,
2	T. Pradee	p, "Nano: The Essentials"	, McGraw -	– Hill ed	ucation	ո, 200	7.			
3		S.S.R. Kumar, Josef I ns, Techniques, Tools, Ap							Toward	ds Biomedical
4	Nicholas A	A. Kotov, "Nanoparticle As	semblies a	and Sup	<u>erstru</u> c	tures"	', CRC, 20	006.		

K.S. Rar	gasamy College of	Technolog	y - Auto	nomou	s Regu	lation		R 20	10	
Department	Nanoscience and Technology	Programme Code & Name				PNT : M.Tech - Nanoscience and Technology				
			Semest	er II						
Cauraa Cada	Course Nor		Ho	ours / W	'eek	Credit	M	aximum N	Marks	
Course Code	Course Nar	ne	L	Т	Р	С	CA	ES	Total	
10 PNT 207	CHARACTERISATI NANOMATERIALS LABORATORY	ON OF	0	0	3	2	50	50	100	
Objective(s)	Understand the difference characterisations of				niques a	and acquire	knowle	dge on th	ne various	

- Particle size determination XRD
- Elemental analysais XRF
- Determination of surface area porosity nanoparticles
- Morphological study of nano particles SEM/ TEM*
- Surface Topographic study of Nanoparticles AFM
- Identification of functional group of nanoparticles FTIR
- Thermal analysis TGA/ DTA
- Contact angle measurements
- Imaging of Nano particles AFM
- Nano Indentation

Total Hrs	45
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K.S. Ra	ngasamy Colle	ege of Tech	nology	- Auton	omous	Regu	lation		R	2008	
Department	Nanoscien Technol		Prog	Programme Code & PNT : M. Name					Tech - Nanoscience and Technology		
		<u> </u>	Semester II								
0 0 1				Hours / Week			Credit		Maximum Marks		
Course Code	Col	Course Name			Т	Р	С	CA	ES	Total	
10 PNT 208	TECHNICA PREPARAT PRESENTA	TON AND		0	0	2	0	100	00	100	
Objective(s)	journals ar	nd confere	nce pro	ceeding						cles in referred rt writing and	
Objective(s) journals and conference proceedings. To improve the technical report writing presentation skills of the students. • Each student is allotted to a faculty of the department by the HOD • By mutual discussions, the faculty guide will assign a topic in the general / subject area to the student. • The students have to refer the Journals and conference proceedings and collect the published literature. • The student is exposed to collect at least 20 such Research papers published in the last 5 years. Methodology Methodology • Using OHP/Power point, the student has to make presentation for 15-20 minutes followed by 10 minutes discussion. • The student has make two presentations, one at the middle and the other near the end of the semester. • The student has to write a Technical report for about 30-50 pages (Title page, One page Abstract, review of research paper under various subheading, Concluding remarks and List of References). The technical report has to b submitted to the HO									nd collect the blished in the 20 minutes her near the e page, One procluding		
	Week Activity										
		Allotment	of Facul	tv Guide	by the						

	Week	Activity
	I	Allotment of Faculty Guide by the HOD
	II	Finalizing the topic with the approval of Faculty Guide
Execution	III-IV	Collection of Technical papers
	V – VI	Mid semester presentation
	VII – VIII	Report writing
	IX	Report Submission
	X-XI	Final presentation

	100 % Continuous Assessment2 Hrs/week	
	Component	Weightage
Evaluation	Phase – I Presentation	25 %
	Phase – II Presentation	25 %
	Report preparation and Submission	30 %
	Final presentation	20 %
	Total	100%

	K.S. Ran	gasamy College of Tech				Regul				2010
Depar	rtment	Nanoscience and Technology		mme Co Name			PNT : I		- Nanos chnology	cience and
			S	emeste	r III					
Cour	se Code	Course Name		Hou	rs / We	ek	Credit		Maximu	m Marks
Cours	se Code	Course Marrie	; 	L	Т	Р	С	CA	ES	Total
10 P	NT 301	NANODEVICES		3	0	0	3	50	50	100
Objective(s) To understand the development of nanoelectronics. To study the principle behind the nanodevices. To explore the application of nanodevices. To understand and study the molecular and bioelectronics on nano application.										
		1 DEVICES					tal Hrs			9
transis array -	stor – Ele - Quantur	onic devices – Electrons ctron wave transistor – n computer- Bit and Qub IG DEVICES	Electron s	pin tran	sistor -	- Qua	ntum cell	lular au	tomata - arallelisr	 Quantum do
Three-	terminal :	ent – Tunnel effect and resonate tunneling devic ates - Digital circuits des	es -Techno	ology of	RTD -	Mem	ory applic	ations -	Basics	
3 S	UPERCO	NDUCTING DEVICES				Tot	tal Hrs		,	9
Josepl Flux q	hson tunn uantum d	scopic characteristics – Neling devices - Elementa evice – LC - Gate – Maç devices – SFQD - RSFQI	ary circuits gnetic flux	Association	ciative n – Qu	or Col antum	ntent – Ad n cellular :	ddressa automa	ıble men	nory - SQUID -
		IN NANODEVICES					tal Hrs		,	9
Heat of Therm	dissipatior al noise	ntegrated electronics - S n – Parameter spread as - Reliability as limiting for es by tunneling and therr	limiting eff actor – Ph	fect – Li	mits du	ue to t	hermal pa	article r	notion -	Debye length -
5 B	SIOELECT	RONICS				Tot	tal Hrs		9	9
and na	anotubes	 Molecular processor – Polymer electronic – S ocessing with chemical r 	elf assemb	oling circ	cuits –	Optica	al molecu	lar mer		
Total h	nours to b	e taught							4	! 5
	ence(s) :									
		P. Glosekotter and J. Quantum Devices", Sprin			electro	nics a	and Nand	osysten	ns-From	Transistors to
		neault, Jean-Michel Lourt			nde, A	riel Le	venson, "	Nanopl	notonics'	, ISTE.
	V.R.Fahrn Springer, 2	er, "Nanotechnology and 2006.	l Nanoelec	tronics -	- Mate	rials,	Devices a	and Me	asureme	nt Techniques

K.S. Ra	ngasamy Colle	ge of Tecl	nnology -	Auton	omous	Regul	ation		R	2010	
Department	Nanoscieno		Progra		Code &		PNT :			cience and	
•	Technol	ogy	<u>.</u>	Name Semeste	er III			Tec	chnology	•	
					ırs / We	ek	Credit		Maximu	m Marks	
Course Code	Cou	rse Name		L	T	P	C	CA	ES	Total	
10 PNT 302	PROJECT WO	ORK - PHA	SE I	0	0	12	2	100	00	100	
Objective(s)										tudents to new practically and	
Methodology	Each By mu to the The si publis The si last 5 Using 10 mil The si of the The si remar	 Each student is allotted to a faculty of the department by the HOD By mutual discussions, the faculty guide will assign a topic in the general / subject area to the student. The students have to refer the Journals and conference proceedings and collect the published literature. The student is exposed to collect at least 25 such Research papers published in the last 5 years. 									
		eek before	the imai p	resent	alion, ai			al Oi the	laculty g	luide.	
	Week	Allotment	of Faculty	, Guida	hy the	Activ	vity				
			the topic				Faculty G	iuide			
Execution	III-IV	,	of Scient				acuity C				
	V – VI		ester prese								
	VII – VIII	Report w									
	IX	•	ubmission								
	X-XI	Final pre	sentation								
		<u> </u>									
		Continuou eek and 2		nent							
			onent						ghtage		
Evaluation	Phase – I Pres								25 %		
	Phase – II Pres								25 %		
	Report prepara		ubmission						80 %		
	Final presentat	ion							20 %		
					Tota	al		1	00%		

K.S. Ra	ngasamy Colle	ge of Tech	nology -	Auton	omous	Regul	ation		R	2010	
Department	Nanoscieno Technolo		,	Name			PNT :		- Nanos chnology	cience and	
			S	Semeste	er IV						
Course Code	Co	urse Name		Ηοι	urs / We	ek	Credit		Maximu	m Marks	
Course Code				L	Т	Р	С	CA	ES	Total	
10 PNT 401	PROJECT \	_		0	0	40	10	50	50	100	
Objective(s)										tudents to new theoretically	
Methodology	pub The last Usin by The end The pag rem one	olished liters student is 5 years. ng Power p 10 minutes student ha I of the sen student ha ge Abstract	exposed of exposed of the second of the seco	to colle student n. wo pres a proje resear erences	ct at lea has to r sentation ect repor ch pape s). The p	st 50 s nake p ns, one of for a er under roject after	such Resoresentate at the national solution and the such as the su	earch pion for	papers put 15-20 min the of es (Title pading, Casubmitte submitter)	oncluding ed to the HOD	
 -	Week	Allatonant	-4 F It-	. 0:	la 4la a . l	Activ	vity				
	<u> </u>		of Faculty				Fooulty O	·ido			
	III-IV	ŭ	•			al Of I	racuity G	uide			
Execution	V – VI		of Scient								
			ster prese	ntation							
	VII – VIII	Report wi									
		IX Report Submission									
	X-XI	Final pres	sentation								

	50 % Continuous Assessment and 50 % En30 hrs/week and 20 credits	nd semester exam
	Component	Weightage
Evaluation	Phase – I Presentation	15 %
	Phase – II Presentation	15 %
	Report preparation and Submission	20 %
	Viva - Voce	50 %
	Total	100%

	ngasamy College of Tecl				Regu				2010
Department	Nanoscience and	_	mme Co	ode &		PNT :			cience and
<u>'</u>	Technology		Name Elective	. I			Tec	chnology	<u>'</u>
						l			
Course Code	Course Name			rs / We	1	Credit			m Marks
			L	Т	Р	С	CA	ES	Total
10 PNT E11	MICRO ELECTRO MECHANICAL SYSTEM NANO ELECTRO MECI		3	0	0	3	50	50	100
	SYSTEM								
Objective(s)	application of NEMS & MEMS								
1 SILICON	TECHNOLOGY				То	tal Hrs		Ç	9
technology – micromechani 2 MICRO E	ntegration -microminiaturized microelectronic and cost for nanoelctronics - interpretation of the cost	mechanic egrated opt SYSTEMS	al syst oelectro	tems onics.	(MEM To	S) – m	icrome	chanics	technology 9
– photolithogra etching – LIG	aphy – ion implantation – o A – x-ray based fabrication ealing – 3D packaging – a	diffusion – d on – packa	oxidatio ging of	n – CV MEMS	'D – F 3 devi	PVD – spu ices–micr	ittering osysten	– single n packag	crystal reactiv ging-packagin
3 DESIGN	OF MEMS				To	tal Hrs		Ç	9
photolithograp thermo mecha methods – cor	lerations – selection of m hy – thin film fabrication – unical stress analysis – dy nputer aided designing.	geometry	shaping		chanio				
			ılysis –	interfa			alysis -		nical designin
	TIONS OF MEMS AND N	EMS			To	tal Hrs	-	(nical designin 9
Micromechanionicomicomicomicomicomicomicomicomicomicom	TIONS OF MEMS AND N cal pressure sensors -Iner cs – micro channel heat vitching – RF MEMS – ME	EMS tial sensors sinks – op MS variabl	s – acce	elerom	To eter – visua	tal Hrs gyroscop al display	pe - piez – prec	zo resisti ision opt	nical designin 9 ve – capacitiv tical platform
Micromechanion optical data swaps NANO EL	TIONS OF MEMS AND Noted pressure sensors -Inerpose — micro channel heat vitching — RF MEMS — MELECTROMECHANICAL SY	EMS tial sensors sinks – op MS variable YSTEMS	s – acce tical ME e capac	elerome EMS – citors –	To eter – visua MEM To	tal Hrs gyroscop al display S switche tal Hrs	pe - piez - prec	zo resisti ision opt sonators.	nical designin 9 ve – capacitiv tical platform
Micromechanion of the micro robotic optical data swamps NANO Elemento Nano	TIONS OF MEMS AND Notal pressure sensors -Inerpose — micro channel heat vitching — RF MEMS — MEMS— MECTROMECHANICAL STANDOR MACHINING OF NETWORK — mano imprint lithography —	EMS tial sensors sinks – op MS variable YSTEMS MS - electe - polymeric	s – acce tical ME e capace ron bea	elerome EMS – citors – am lithe	To eter – visua MEM To ograp	tal Hrs gyroscop al display S switche tal Hrs hy – Nar es – focu	pe - piez - preces - Res no elec	zo resisti ision opt sonators. tromecha	nical designin 9 ve – capacitiv tical platform 9 anical system - wet chemica
Micromechanion of the control of the	TIONS OF MEMS AND Noted pressure sensors -Inerpose — micro channel heat vitching — RF MEMS — MEMS—ECTROMECHANICAL STAND and machining of NEMB — mano imprint lithography—cil lithography and sacrific	EMS tial sensors sinks – op MS variable YSTEMS MS - electe - polymeric	s – acce tical ME e capace ron bea	elerome EMS – citors – am lithe	To eter – visua MEM To ograp	tal Hrs gyroscop al display S switche tal Hrs hy – Nar es – focu	pe - piez - preces - Res no elec	zo resisti ision opt sonators. g tromecha n beam lenges -	nical designin 9 ve – capacitiv tical platform 9 anical system - wet chemica
Micromechanic micro robotic optical data sw 5 NANO EL Introduction — fabrication — stender to tall hours to	TIONS OF MEMS AND Noted pressure sensors -Inerposes — micro channel heat vitching — RF MEMS — MELECTROMECHANICAL SYNAMORE INTERPOSE — mano machining of NEMB — mano imprint lithography—cill lithography and sacrificate the sacrificate in the s	EMS tial sensors sinks – op MS variable YSTEMS MS - electe - polymeric	s – acce tical ME e capace ron bea	elerome EMS – citors – am lithe	To eter – visua MEM To ograp	tal Hrs gyroscop al display S switche tal Hrs hy – Nar es – focu	pe - piez - preces - Res no elec	zo resisti ision opt sonators. g tromecha n beam lenges -	nical designin 9 ve – capacitiv tical platform 9 anical system - wet chemical
Micromechanic - micro robotic optical data swap 5 NANO EL Introduction – fabrication – retching – stendal hours to Reference(s):	TIONS OF MEMS AND Noted pressure sensors -Inerposes — micro channel heat vitching — RF MEMS — MELECTROMECHANICAL SYNAMORE INTERPOSE — mano machining of NEMB — mano imprint lithography—cill lithography and sacrificate the sacrificate in the s	EMS tial sensors sinks – op MS variable YSTEMS MS - electe polymeric al etching -	s – acce tical MI e capace ron bea : nano f – large s	elerome EMS — citors — am lith fiber te scale in	To eter – visua MEM To ograp emplat ntegra	tal Hrs gyroscop al display S switche tal Hrs hy – Nar es – focu	pe - piez - prec s - Res no elec used iou	zo resisti ision opt sonators. (tromechan beam lenges -	nical designing ye – capacitive tical platform genical system - wet chemical applications.
Micromechanic - micro robotic optical data sw 5 NANO EL Introduction - retching - stendard hours to Reference(s): K. Goser Molecular	TIONS OF MEMS AND Notal pressure sensors -Inerpose — micro channel heat vitching — RF MEMS — MEMS—ECTROMECHANICAL SY nano machining of NEM nano imprint lithography—cil lithography and sacrificate the taught — P. Glosekotter and J.	EMS tial sensors sinks – op MS variable YSTEMS MS - electe polymeric al etching -	s – acce tical MI e capac ron bea nano f large s	elerome EMS – citors – am lith fiber te scale in	To eter – visua MEM To ograp emplat ntegra	tal Hrs gyroscop al display S switche tal Hrs hy – Nan es – focu tion – futu	pe - piez precess – Res no electure chal	zo resisti ision opt sonators. (tromechan beam lenges - 4	nical designing ye – capacitive tical platform anical system - wet chemical applications. Transistors to
Micromechanic - micro robotic optical data sw 5 NANO EL Introduction – fabrication – retching – stendal hours to Reference(s): K. Goser Molecular	TIONS OF MEMS AND Notal pressure sensors -Inerpose - micro channel heat vitching - RF MEMS - MEDICAL STATE - MEMS - MEDICAL STATE - MEMS - MEM	EMS tial sensors sinks – op MS variable YSTEMS MS - electe polymeric ial etching - Dienstuhl, ger, 2004.	s – acce tical MI e capace ron bea : nano f - large s "Nanoel	elerome EMS – citors – am lith fiber te scale in	To eter – visua MEM To ograp emplat ntegra ics ar	tal Hrs gyroscop al display S switche tal Hrs hy — Nan es — focution — futu nd Nanos	pe - piez - prec s - Res no elec used ion ure chal	zo resisti ision opt sonators. stromecha n beam lenges - 4 - From	nical designing ye – capacitive tical platform anical system wet chemic applications. Transistors for the platform of the

K.S. F	≀ang	asamy College of Tech				Regul				2010
Department	t	Nanoscience and Technology	•	mme C Name	ode &		PNT : I		 Nanos chnology 	cience and
				Elective	e l					
				Hou	rs / We	ek	Credit		Maximu	m Marks
Course Co	de	Course Name	!	L	Т	Р	С	CA	ES	Total
10 PNT E1	2	DRUG DELIVERY		3	0	0	3	50	50	100
Objective(s)	To provide exposure to therapy and drug deliver								
1 IMAGIN	NG T	ECHNIQUES				To	tal Hrs		9	9
		tics - Imaging - MRI -								
		Operation and imaging	- Nanotech	nology	based			luding i		
		ACTIVE GLASSES	D				al Hrs			9
	mea	ano Bioactive glasses – surement of bioactivity ons.								
3 CANCE	ER T	REATMENT				Tot	al Hrs		(9
particulate ta	arge	 Vaccine immunothera ting. MECHANISM 	py – Radio	otherapy	/ – The		erapy – F	Photo d		herapy – Nano
		ibody conjugated nanop	articles (Conjuga	tod na			raction		
 Biomedica 	al na	anoparticles – Liposome olymers – Applications.								
		D DRUG DELIVERY				Tot	al Hrs		(9
strategies fo	r tar	ial pharmacology – stra geted delivery – by hum – macrophage targeting	an – oral d							
Total hours	to be	e taught							4	! 5
Reference(s	5):									
1 Challa	Kum	ar, Nanomaterials for me	edical diag	nosis aı	nd ther	apy , \	Wiley VCI	H 2005		
		Schwarz, Cristian I. Co logy" CRC Press, 2004.	ontescu, k	Carol P	utyera,	"Dek	ker ency	clopedi	a of na	noscience and
		raetorius and Tarun K. N								
4 Oncol		Yezhelyev, Xiaohu Gad				•••		-		
5 Drug D	elive	Chen, "Micro and nan ery Reviews, 56 (1621-16	33) 2004.		•				Ū	•
		d Jiang Chang, Prepara ated sol–gel method, Ma						tive-gla	isses (NI	BG) by a quick

	K.S. Rar	ngasamy College of	Technology	- Auton	omous	Regu	lation		R 20	10
Dε	epartment	Nanoscience and Technology	Programm	ne Code	& Name)	PNT : M	Tech - N. Techr	Nanoscien ology	ice and
				Electiv	е					
Col	uraa Cada	Course Na	ma	Hou	rs / We	ek	Credit	M	aximum N	/larks
C01	urse Code	Course Na	me	L	Т	Р	С	CA	ES	Total
10	PNT E13	FUNDAMENTALS BATTERIES		3	0	0	3	50	50	100
Ob	ojective(s)	With the present of energy storage systems solving different kin of the course the stand their uses.	stem for the ds of problem	future to	ends. T	This co energy	ourse give storage sy	s fundai /stem te	mental co chnology.	ncepts for At the end
1	PRINCIPL	ES OF OPERATION	I			То	tal Hrs		9	
Volta Batt of B	age, Capac ery Perform atteries.	-Components & Cla ity, and Energy-Spe ance-Battery standar	cific Energy	and Ene	rgy De	nsity o eral Ch	of Practica naracteristi	l Batteri	es-Factor tion and	s affecting
2		BATTERIES es-Introduction-Class					tal Hrs		9	
3 Res Mag Amb	eries-Solid e RESERVE erve batter gnesium war bient temper	ir batteries-Button co electrolyte batteries. BATTERIES & SOD ries-Introduction-Claster activated batterie fature lithium anode	IUM BETA B sification of es-Zinc/silver	ATTERIE reserv oxide re	ES e batte	To eries-c batteri	tal Hrs haracteris es-Spin d	tics of ependen	9 reserve t reserve	
4				11163-1116	imai ba	allenes	5-50ululli-L			batteries-
	and application. 4 SECONDARY BATTERIES Secondary batteries-Introduction-General characterisation and application of secondary batteries-Types and characteristics of secondary batteries-Lead acid batteries-Valve regulated lead-acid batteries-Iron electrode batteries-Nickel cadmium batteries and its types-Nickel/zinc batteries-Zinc/carbon rechargeable batteries-									
char batte	racteristics o eries-Nickel	eries-Introduction-Ge of secondary batterie	neral charac es-Lead acid and its type	terisatior batterie	and a s-Valve	To pplicat regula	tal Hrs ion of sec ated lead-	condary acid bat	9 batteries- teries-Iron	batteries- ery design Types and electrode
char batte Nick 5	racteristics of eries-Nickel cel metal hyd METAL-AI	eries-Introduction-Ge of secondary batterie cadmium batteries dride batteries-Lithiun R BATTERIES & PO	neral charactes-Lead acid and its typen-lon batterie	terisation batterie es-Nickel s- EL CELL	and a s-Valve l/zinc b	To pplicat regula atterie To	tal Hrs ion of sec ated lead- s-Zinc/carl tal Hrs	condary acid bati oon rech	9 batteries- teries-Iron nargeable 9	batteries- ery design Types and electrode batteries-
char batte Nick 5 Gen Gen	racteristics of eries-Nickel cel metal hyd METAL-AI neral charact neral charact	eries-Introduction-Ge of secondary batterie cadmium batteries dride batteries-Lithiun	neral charactes-Lead acid and its typen-lon batterieeRTABLE FUEZinc-Aluminiu	terisation batteries es-Nickel s- EL CELLS m-Magno cell-Inno	and a s-Valve by since by since by since by since by since by since continue of the since of the	To pplicat regula atterie To ithium design	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v	condary acid bate boon rech ries-Fue vattage f	9 batteries- teries-Iron nargeable 9 I cells-In uel cells.	Types and electrode batteries-troduction-Applicable
char batte Nick 5 Gen Gen fuel	racteristics of eries-Nickel cel metal hyd METAL-AI neral charact neral charact	eries-Introduction-Ge of secondary batteries cadmium batteries dride batteries-Lithium R BATTERIES & PO cteristics-Chemistry-Z teristics and Operation ogies-System require	neral charactes-Lead acid and its typen-lon batterieeRTABLE FUEZinc-Aluminiu	terisation batteries es-Nickel s- EL CELLS m-Magno cell-Inno	and a s-Valve by since by since by since by since by since by since continue of the since of the	To pplicat regula atterie To ithium design	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v	condary acid bate boon rech ries-Fue vattage f	9 batteries- teries-Iron nargeable 9 I cells-In uel cells.	Types and electrode batteries-troduction-Applicable
char batte Nick 5 Gen Gen fuel Tota	racteristics of eries-Nickel kel metal hyd METAL-Al heral characteral characteral technological received in the cell tech	eries-Introduction-Ge of secondary batteries cadmium batteries dride batteries-Lithium R BATTERIES & PO cteristics-Chemistry-Z teristics and Operation ogies-System require	neral charactes-Lead acid and its typen-lon batterieeRTABLE FUEZinc-Aluminiu	terisation batteries es-Nickel s- EL CELLS m-Magno cell-Inno	and a s-Valve by since by since by since by since by since by since continue of the since of the	To pplicat regula atterie To ithium design	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v	condary acid bate boon rech ries-Fue vattage f	9 batteries- teries-Iron nargeable 9 I cells-In uel cells. are & perf	Types and electrode batteries-troduction-Applicable
char batte Nick 5 Gen Gen fuel Tota	racteristics of eries-Nickel kel metal hydrometal characterial characterial characterial technological hours to be erence(s):	eries-Introduction-Ge of secondary batteries cadmium batteries dride batteries-Lithium R BATTERIES & PO cteristics-Chemistry-Z teristics and Operation ogies-System require	neral charactes-Lead acid and its type n-lon batterie RTABLE FUE Zinc-Aluminiu on of the fuel ments-Fuel p	terisation batterie es-Nickel s- EL CELLS m-Magno cell-Inno	and a s-Valve //zinc b	To pplicat regula atterie To ithium design rage te	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v	condary acid bat con rech ries-Fue vattage f s-Hardwa	9 batteries- teries-Iron nargeable 9 I cells-In uel cells. are & perf 45	Types and electrode batteries-troduction-Applicable
char batte Nick 5 Gen Gen fuel Tota Refe	racteristics of eries-Nickel kel metal hydrometal characteristics cell technologial hours to be erence(s):	eries-Introduction-Ge of secondary batterie cadmium batteries dride batteries-Lithiun R BATTERIES & PO cteristics-Chemistry-Zeristics and Operatio ogies-System require e taught	neral charactes-Lead acid and its type n-lon batterie. RTABLE FUE Zinc-Aluminium of the fuel ments-Fuel p	terisation batterie es-Nickel s- EL CELL: m-Magno cell-Inno rocessin	and a s-Valve b/zinc b S esium-L ovative o g & stor	To pplicat regula atterie To ithium design rage te	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v chnologies	condary acid bate con rech ries-Fue vattage f s-Hardwa	9 batteries- teries-Iror nargeable 9 I cells-In uel cells. are & perf 45	Types and electrode batteries-troduction-Applicable
char batte Nick 5 Gen Gen fuel Tota Refe	racteristics of eries-Nickel kel metal hydrometal characterial characterial characterial characterial characterial characterial hours to be erence(s): Thomas R Ogumi Z, " Dudney N,	eries-Introduction-Ge of secondary batterie cadmium batteries dride batteries-Lithiun R BATTERIES & PO cteristics-Chemistry-Zeristics and Operatio ogies-System require e taught eddy, "Linden's Hand	neral charactes-Lead acid and its type n-lon batterie. RTABLE FUE Zinc-Aluminium of the fuel ments-Fuel publication of Batteriology (General Water Batteriology)	terisation batterie es-Nickel s- EL CELLS m-Magne cell-Inno rocessin eries", Me ral)", The	a and a s-Valve //zinc b S esium-L ovative o g & stor	To pplicat regula atterie To ithium design rage te	tal Hrs ion of sec ated lead- s-Zinc/carb tal Hrs -air batte s for low v chnologies fessional, cal Society	condary acid battoon rech ries-Fue vattage f s-Hardwa USA, 20	9 batteries-from argeable 9 I cells-In uel cells. are & perf 45 10.	Types and electrode batteries-troduction-Applicable

K.S. Ra	ngasamy College of	Technology	- Auton	omous	Regu	lation		R 20	10
Department	Nanoscience and Technology	Programm	ne Code	& Name)	PNT : M.	Tech - N. Techn	lanoscien ology	ce and
			Elective	Э					
Course Code	Course No		Hou	rs / We	ek	Credit	M	aximum N	/larks
Course Code	Course Na	me	L	Т	Р	С	CA	ES	Total
10 PNT E14	NANOTECHNOLO POLYMERS	GY IN	3	0	0	3	50	50	100
Objective(s)	With the present of develop effective per and application technologically. At concepts in several	erformance for solving the end of the	or the fut different ne course	ure tren t kinds e the st	ds. The of udents	is course of problems would be	gives fur that p acquai	idamental oolymers	concepts involving
1 INTRODU	JCTION TO POLYME					tal Hrs		9	
polymers, mici	oolymers in top – dow o structures in polyr olymers in nanotechn	mers – polyr	ner leng	ıth, mol	ecular	weight, a	amorpho	us and c	rystalline,
	TING POLYMERS					tal Hrs		9	
and morpholog	otion – band theory m y- theory of conductiv s)s - polymers with me	ity, Conductio	n mecha	anism, u	ses -				
3 POLYME	R FUNCTIONALITY				То	tal Hrs		9	
	g polymers - polymer i meric fibers, polymers,				olymer	nanocom	oosite fro	m polyme	erization -
	APPLICATIONS					tal Hrs		9	
and morpholog	electrospinning- produ gy of nanofibers - ele fibers – Nanofibers ir	ectro static se	elf asser	nbled n	anolay	er films f			
5 ORGANIC	C ELECTRONIC APPI	LICATIONS			То	tal Hrs		9	
	tterning techniques - nsistor from micro to								
Total hours to b	pe taught							45	
Reference(s):							•		
1 Harry R a education	llcock, Frederick W la , 2003	mpe and Jam	ies E Ma	rk," Cor	ntempo	rary polyn	ner chem	nistry", pe	rson
2 K cousins	, keith cousins," polyn	ners in electro	onics" sm	ithers F	Rapra t	echnology	publish	ers, 2006	
3 P J Brown	n and K Stevens," nan	ofibers and n	anotechr	nology i	n textil	es" CRC p	ress, 20	07	
4 Frances 0	Gardiner, Eleanor cart	er,: polymer e	electronic	s – a fle	exible t	echnology	r", ismith	ers, 2009	

	K.S. Ran	ngasamy College of	Technology	- Auton	omous	Regu	lation		R 20	10	
De	partment	Nanoscience and Technology	Programm	ne Code	& Name)	PNT : M.	Tech - N Techn	lanoscien ology	ce and	
				Elective	Э						
	0 1	0 N		Hou	rs / We	ek	Credit	M	aximum N	/larks	
Col	urse Code	Course Na	me	L	Т	Р	С	CA	ES	Total	
10	PNT E15	SOLID STATE OF NANOTECHNOLO	GY	3	0	0	3	50	50	100	
1		PROPERTIES					tal Hrs		9		
mate	Melting point and phase transition processes, Physics of Amorphous Material: preparation of amorphous materials, Size-induced metal-insulator-transition (SIMIT)- nano-scale magnets-order and magnetic structure, chemical physics of atomic and molecular clusters.										
2		CHEMISTRY OF S					tal Hrs		9		
		 chemical potential electric potential at th 								n- surface	
3		RY ASPECTS					tal Hrs		9		
Sem		Photoconductivity-E Nanostructures-Tra catalysis.									
4	NANOSTR	UCTURES				To	tal Hrs		9		
nan		cture of Nanopar clusters of metals a								mensional honons in	
5	PROCESS	SING OF METALS AN	ND CERAMIC	POWD	ERS	То	tal Hrs		9		
		characterization of page 5 se Composites : Met						ical work	king. Pro	duction of	
Tota	I hours to be	e taught							45		
Refe	erence(s):										
1	K.W. Kolas	sinski, "Surface Scier	ce: Foundation	ons of Ca	atalysis	and N	anoscienc	e", Wiley	[,] 2002.		
2	Joel I. Gers	sten, "The Physics ar	nd Chemistry	of Mater	ials", W	iley, 20	001.				
A. S. Edelstein and R. C. Cammarata, "Nanomaterials: Synthesis, Properties and Applications", Institute of Physics Pub., 1998.											
4	_	d P.Shen: "Physics a						•			
5		nanabhan, "Mechanio g, A 304-306 (2001)		of Nano	structur	ed Ma	terials", M	aterials S	Science a	nd	

	K.S. Rar	gasamy College of	Technology	- Auton	omous	Regu	lation		R 20	10
De	partment	Nanoscience and Technology	Programm	ne Code	& Name	Э	PNT : M.	Tech - N. Techn	lanoscien ology	ce and
				Elective	Э					
0	0	O a coma a Nia		Hou	rs / We	ek	Credit	М	aximum N	/larks
Col	urse Code	Course Na	me	L	Т	Р	С	CA	ES	Total
10	PNT E16	NANOTECHNOLO SEMICONDUCTOR		3	0	0	3	50	50	100
1	SEMICON	DUCTOR FUNDAME	NTALS		•	To	tal Hrs		9	•
Intro	duction to S	Semiconductor physi	cs - Semico	nductor	nanosti	ructure	s – Electr	onic stru	ucture and	d physical
proc	ess – Princi	ples of semiconducto	r nanostructu	ıres base	ed elect	ronic a	ind electro	-optical	devices	
2		I CONFINED MATER					tal Hrs		9	
tran	sitions-fluore	 optical transition escence/ luminesce ence emission. 								
3	SEMICON	DUCTOR NANOPAR	TICLES - AI	PPLICAT	IONS	То	tal Hrs		9	
Opti	cal lumines	cence and fluoresce	ence from d	irect bar	nd gap	semio	conductor	nanopai	ticles, su	rface-trap
pass	sivation in	core-shell nanopart	icles, carrie	r injecti	on, po	lymer-	nanopartic	le, LED	and so	olar cells,
elec	troluminesce	ence, barriers to n	anoparticle I	asers, c	doping	nanop	articles, N	√n-Zn-S	e phosph	nors, light
emis	ssion from in	direct semiconductor	s, light emiss	sion form	Si nan	odots.				
4	SEMICON	DUCTOR NANOWIR	ES			То	tal Hrs		9	
	rication strat oribbons, na	egies, quantum cond nosprings.	ductance effe	ects in se	emicono	ductor	nanowires	, porous	Silicon, r	nanobelts,
5	SEMICON	DUCTOR NANODEV	'ICES			То	tal Hrs		9	
Sing	le-Electron ocomputers:	Devices; Nano scale Dynamics; Nanoro : Theoretical Models nodevices; Gas-Base	botics and s; Optical Fi	Nanoma	anipulat Nanod	tion; Nevices	Mechanica ; Photoch	I Molec	ular Nar	odevices;
Tota	l hours to be	e taught							45	
Refe	erence(s):									
1	Hari Singh	Nalwa, "Encyclopedi	a of Nanotec	hnology"	', USA 2	2011				
2	Bharat Bhu	ısan, "Springer Hand	book of Nand	technolo	ogy", sp	ringer,	Newyork,	2007		
3	sons, 2010									
4		P. Glosekotter and Quantum Devices", S			electron	nics ar	nd Nanosy	/stems-F	rom Tran	sistors to

K.	S. Rang	asamy College of Tech	nology - A	Autono	mous	Regul	ation		R	2010
Departm	nent	Nanoscience and	•	mme C	ode &		PNT : I			cience and
Боранн	10111	Technology		Name	11			Ted	chnology	
			l l	Elective			T			
Course	Code	Course Name	9		rs / We		Credit			m Marks
				L	Т	Р	С	CA	ES	Total
10 PNT	Γ E21	NANOSAFETY AND ENVIRONMENTAL IS:		3	0	0	3	50	50	100
Objecti	ive(s)	To provide exposure to technology. To explore the various issues on e	the toxic e	effects o	of nano	techn	ology on	human	health a	nd life, analyze
1 INT	RODUC	TION				To	tal Hrs		!	9
- Prediction and policing and policing NAI Inhalatio	ds – Saf ting haz cy makin NOTOXI n of na e Solids	Nano - Specific Risks- R ety – transportation of ard – Materials Characting- ig- Ecotoxicity measurer ICOLOGY Inomaterials – Overvier – Bio –persistence of	NP - Emergerization. Rement of Power w. Introduction	gency realisk Ass lychlirin ction- I	espond essme ated bi nhalati terial.	lers. F nt rela pheny Toton de Syste	Risk assestated to naid and intestal Hrs eposition mic Tren	ssment inotech ermedia and P slocatio	-Environ nology - tes in the ulmonary on of inh	nmental Impact Environmental eir degradation 9 y clearance of naled Particles.
		ets of SWCNT- Pulmor								Interactions of
-	-	nmation with oxidative st	ress – inte	ractions	OT SV			cropnaç		0
		NTAL ISSUES posure and systematic			f + -		tal Hrs	-1-4-		9
Experime exposure	ental da e throug	and cardiovascular toxi ta. Toxicity of polymeric h the indoor air environn	nanopartic	les with	respe	ct to tl door c	neir applion of PM and	cation a	s drug c mental s	arriers. Particle tudy.
	HICS						tal Hrs			9
nanotech potential aspects nanotech	hnologie risks – of poter hnology.		ence – gei ssessment	neral be of exp	enefits osure	- ber to the	nefits for e nanote gy – Lega	health chnolog	and med gy. Bioet atory co	dical practice – thics and legal nsiderations of
		SES AND FUTURES	 				tal Hrs			9
Worke	ers prote	 the frame of worker treetion — International dought upational risk assessme 	ocuments -	- prote	ction o	f med	lical staff	- Nur		
Total hou	urs to be	taught	<u> </u>							ŀ5
Reference	ce(s):									
		nova, N. Opopol and Mringer 2006.	I.I. Luster,	"Nanote	echnolo	gy -	Toxicolog	ical Iss	ues and	Environmental
₂ Vind	od Labh	asetwar and Diandra L USA, 2007 .	. Leslie, "B	iomedic	al App	licatio	ons of na	notechr	nology",	A John Willy &
		.; et.al Toxicity of Single	-Walled Ca	arbon Na	anohor	ns. A	CS Nano	2 (213-	-226) 20	08.
₄ Hut	chison,	J. E. Green Nanosciers of Nanotechnology. AC	nce: A Pro	active A	Approa	ch to				
₅ Mo-	-Tao Zhu	u et.al Comparative stud ogy, 21 (102-111) 2008.	ly of pulmo				ano- and	submic	ron-size	d ferric oxide in
₆ Dra	cy J. Ge	entleman, Nano and Env 39, 2009.	ironment: E	Boon or	Bane?	Envi	ronmenta	I Scien	ce and te	echnology,

	K.S. Ran	gasamy College of Tech	nology -	Autono	mous	Regul	ation		F	R 20	10		
Dep	partment	Nanoscience and Technology	Progra	mme Co Name	ode &		PNT :		- Nanos chnology		ice and		
				Elective	II	•			<u> </u>				
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Cou	rse Code	Course Name		L	Т	Р	С	CA	ES		Total		
10 F	PNT E22	INTELLECTUAL PROPERIGHTS	RTY	3	0	0	3	50	50		100		
Obj	ective(s)	To provide awareness property.	about IP	Rights.	То	provid	e exposi	sure to protect the Intellec					
1	INTRODU	ICTION				Tot	al Hrs			9			
		nvention and Creativity - I Novable Property ii. Immov							ion of IP	PR -	Basic types		
2		REGISTRATION					al Hrs			9			
Defi	nitions - In	Copyrights and related r dustrial Designs and Inteq vels - Application Procedu	grated circ										
3	INTELLEC	CTUAL PROPERTY				Tot	al Hrs			9			
		onvention relating to Inte ral Agreement on Trade a			Estab	olishme	ent of W	IPO -	Mission	and	Activities -		
4	STRATEG	SIES				Tot	al Hrs			9			
		Vs WTO and Strategies								Orc	linance and		
		of a national Intellectual Pr	roperty Pol	licy - Pre	esent a			mpetiti					
5	CASE ST						al Hrs			9			
Indu	strial desig	on - Patents (Basumati rion In and Integrated circuits -											
Tota	I hours to b	pe taught							•	45			
Refe	erence(s):												
1	N.R. Subb Pvt. Ltd.,	oaram," Handbook of India 1998.	n Patent L	aw and	Practi	ce ", S	. Viswan	athan (Printers	and	Publishers)		
2	Eli Whitne	y, United States Patent N	umber: 72	X, Cotto	n Gin,	March	14, 1794	1.					
3	Intellectua	I Property Today: Volume	8, No. 5, I	May 200	1. [ww	w.ipto	dav.com		_				

	K.S.	Rangasamy College of	f Technology	- Auto	nomo	ıs Reg	ulation			R 2010
De	partment	Nanoscience and Technology	Programme	Code 8	Name	F	PNT : M.1			ence and
			Elect	tive II						
	0 1	0 11		Hou	urs / W	eek	Credit	ľ	b, exploratory resesteps. Data collenterview, mail such as 9 I's Semantic Differ simple random sand cluster sampling. 9 per between two medical per simple random sand cluster sampling. 9 per between two medical per simple random sand cluster sampling. 9 per between two medical per simple random sand scaling, college set per simple random sand simple random sand sand sand sand sand sand sand sand	Marks
Col	urse Code	Course Nar	ne	L	Т	Р	С	CA	ES	Total
10	PNT E23	RESEARCH METHOD ENGINEERING AND MANAGEMENT STUD		3	0	0	3	50	50	100
1	RESEARC	H METHODOLOGY				To	tal Hrs.			9
meth quest 2	ods- Primar tionnaire des SCALES A	y data – observation ign. Secondary data- int ND MEASUREMENTS	method, peternal sources	rsonal of data	interv , exter	iew, te nal sou To	elephonic rces of d tal Hrs.	inter ata.	view, m	ail survey,
scale with	, Likert scale replacement,	ement, Types of scale , Q- sort scale. Samplir simple random sampl ng method – conveniend	ng methods- P ing without re	robabil placem	ity sam ient, si	npling r tratified	nethods samplin	– simp ıg, clus	le randor	m sampling
3	HYPOTHE	SES TESTING				To	tal Hrs.			9
		g – Testing of hypothes tailed tests), Concernir						ence b	etween t	wo means -
4	SAMPLE T	ESTS				To	tal Hrs.			9
rando		sts- One sample tests sample tests – Two sa								
5	ANALYSIS	AND REPORT				To	tal Hrs.			9
		isciminant analysis, F riting- Types of report,								
Total	hours to be t	taught							4	1 5
Refe	rence(s):									
1.	2009.	R., Research Methodo	0 ,			•	•		cations,	New Delhi,
2.	Panneersel	vam, R., Research Met	hodology, Prer	ntice-H	all of In	ndia, Ne	ew Delhi,	2004.		

K.S.Rangasamy College of Technology - Autonomous Regulation									R 2010	
Department	Nanoscience and Programme Code & Technology Name			ı	PNT : M.1	Nanoscie nology	ence and			
		Elect	tive II							
Course Code	Course Name		Hours / Week			Credit Maxim		Maximum	um Marks	
Course Code			L	Т	Р	С	CA	ES	Total	
10 PNT E24	RESEARCH METHODOLOGY - SCIENCE AND HUMANITIES		3	0	0	3	50	50	100	
RESEARCH METHODOLOGY						Total Hrs		9		
Research Methods Versus Methodology-Objectives of Research-Types of Research-Research Approaches-Criteria of Good Research-Hypothesisation-Selection of Topic										
2. DATA CC	LECTION & COMPILING					Total Hrs		9		
Collection of Pr Evaluating Sour	mary Data-Collection of S ces	econdary Da	ta-Inter	view m	nethod-	Compilin	g a W	orking Bi	bliography-	
	MECHANICS OF WRITING					Total Hrs		9		
Spelling-Punctuation-Abbreviations-Margins and Spacing – Heading and Title-Page Numbers-Corrections and Insertions										
4. DOCUME	DOCUMENTATION					Total Hrs			9	
Preparing the list of works cited - Citing Sources in the text- Endnotes and footnotes-Parenthetical References.										
5. PLAGIAR	PLAGIARISM					Total Hrs			9	
Definition – F Infringement-Co	orms of Plagiarism – (llaborative work	Consequence	s of	Plagiar	ism- I	Jnintentio	onal F	Plagiarisn	n-Copyright	
Total hours to be taught								45		
Reference(s):										
1. Joseph Gibaldi, "MLA Handbook for Writers of Research Papers', Modern Language Association of America, 2009										
2004	Wayne Goddard and Stuart Melville, "Research Methodology – An Introduction', Juta and Company Ltd, 2004									
Ranjit Kur	Ranjit Kumar, "Research Methodology", Sage Publications, 1999.									